



PATENT
0397-0404P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant:	H. TAKEUCHI et al.	Conf.:	4024
Appl. No.:	09/541,089	Group:	1762
Filed:	March 31, 2000	Examiner:	M. PADGETT
For:	PLASMA PROCESSING METHOD		

#9/10/02
H. Takeuchi
9/22/02

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REPLY UNDER 37 C.F.R. § 1.111

Assistant Commissioner for Patents
Washington, DC 20231

July 15, 2002

Sir:

In reply to the Office Action mailed February 13, 2002, the period for reply having been extended two (2) months to July 13, 2002, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE CLAIMS:

Please cancel claims 2 and 3 without prejudice or disclaimer of the subject matter contained therein.

Please amend the claims as follows:

1. (Amended) A plasma processing method for performing film formation, etching, or surface treatment on a substrate by supplying high frequency power between an electrode and a holder, by which the substrate is supported to be opposed to the electrode,

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